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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	18625
Number of Logic Elements/Cells	149000
Total RAM Bits	7014400
Number of I/O	586
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA
Supplier Device Package	1156-FPBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-150ea-6fn1156itw

Architecture Overview

Each LatticeECP3 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sys-DSP™ Digital Signal Processing slices, as shown in Figure 2-1. The LatticeECP3-150 has four rows of DSP slices; all other LatticeECP3 devices have two rows of DSP slices. In addition, the LatticeECP3 family contains SERDES Quads on the bottom of the device.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and Programmable Functional Unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

The LatticeECP3 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18Kbit fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, LatticeECP3 devices contain up to two rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The LatticeECP3 devices feature up to 16 embedded 3.2 Gbps SERDES (Serializer / Deserializer) channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of four SERDES channels, along with its Physical Coding Sub-layer (PCS) block, creates a quad. The functionality of the SERDES/PCS quads can be controlled by memory cells set during device configuration or by registers that are addressable during device operation. The registers in every quad can be programmed via the SERDES Client Interface (SCI). These quads (up to four) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the LatticeECP3 devices are arranged in seven banks, allowing the implementation of a wide variety of I/O standards. In addition, a separate I/O bank is provided for the programming interfaces. 50% of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3.

The LatticeECP3 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The LatticeECP3 architecture provides two Delay Locked Loops (DLLs) and up to ten Phase Locked Loops (PLLs). The PLL and DLL blocks are located at the end of the EBR/DSP rows.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located toward the center of this EBR row. Every device in the LatticeECP3 family supports a sysCONFIG™ port located in the corner between banks one and two, which allows for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The LatticeECP3 devices use 1.2 V as their core voltage.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals. A 16x2-bit pseudo dual port RAM (PDPR) memory is created by using one Slice as the read-write port and the other companion slice as the read-only port.

LatticeECP3 devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in LatticeECP3 devices, please see TN1179, [LatticeECP3 Memory Usage Guide](#).

Table 2-3. Number of Slices Required to Implement Distributed RAM

	SPR 16X4	PDPR 16X4
Number of slices	3	3

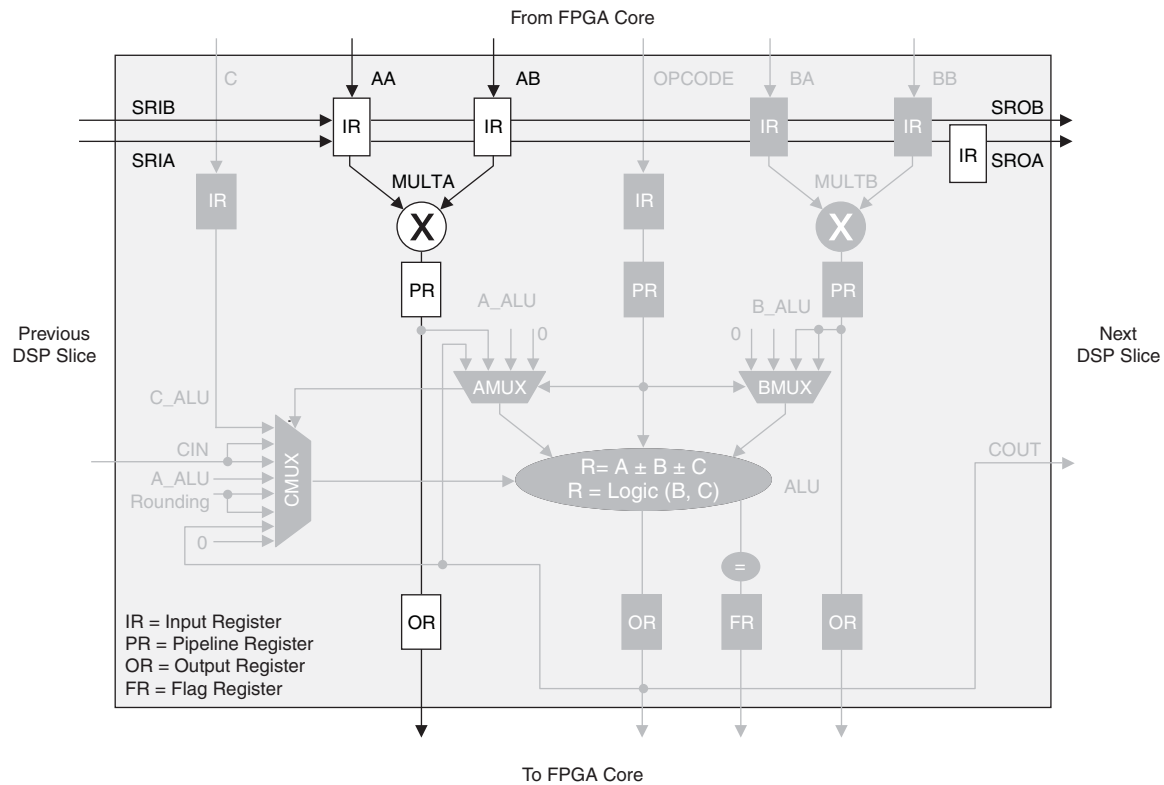
Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

For further information, please refer to TN1182, [LatticeECP3 sysDSP Usage Guide](#).

MULT DSP Element

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, AA and AB, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-26 shows the MULT sysDSP element.

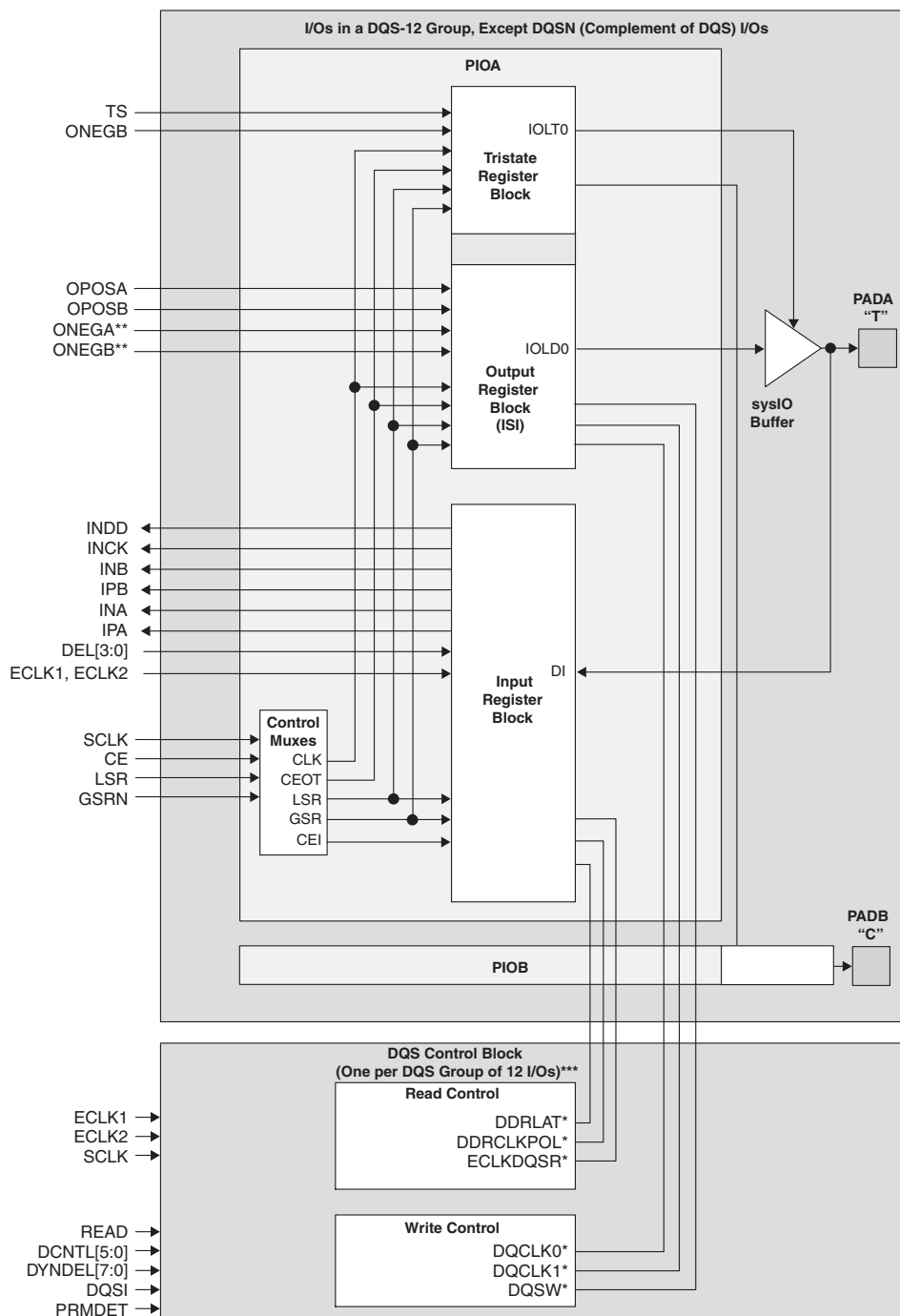
Figure 2-26. MULT sysDSP Element



Programmable I/O Cells (PIC)

Each PIC contains two PIOs connected to their respective sysI/O buffers as shown in Figure 2-32. The PIO Block supplies the output data (DO) and the tri-state control signal (TO) to the sysI/O buffer and receives input from the buffer. Table 2-11 provides the PIO signal list.

Figure 2-32. PIC Diagram



* Signals are available on left/right/top edges only.

** Signals are available on the left and right sides only

*** Selected PIO.

Input signals are fed from the sysI/O buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In single data rate (SDR) the data is registered with the system clock by one of the registers in the single data rate sync register block.

In DDR mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (ECLKDQSR) in the DDR Memory mode or ECLK signal when using DDR Generic mode, creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

A gearbox function can be implemented in each of the input registers on the left and right sides. The gearbox function takes a double data rate signal applied to PIOA and converts it as four data streams, INA, IPA, INB and IPB. The two data streams from the first set of DDR registers are synchronized to the edge clock and then to the system clock before entering the core. Figure 2-30 provides further information on the use of the gearbox function.

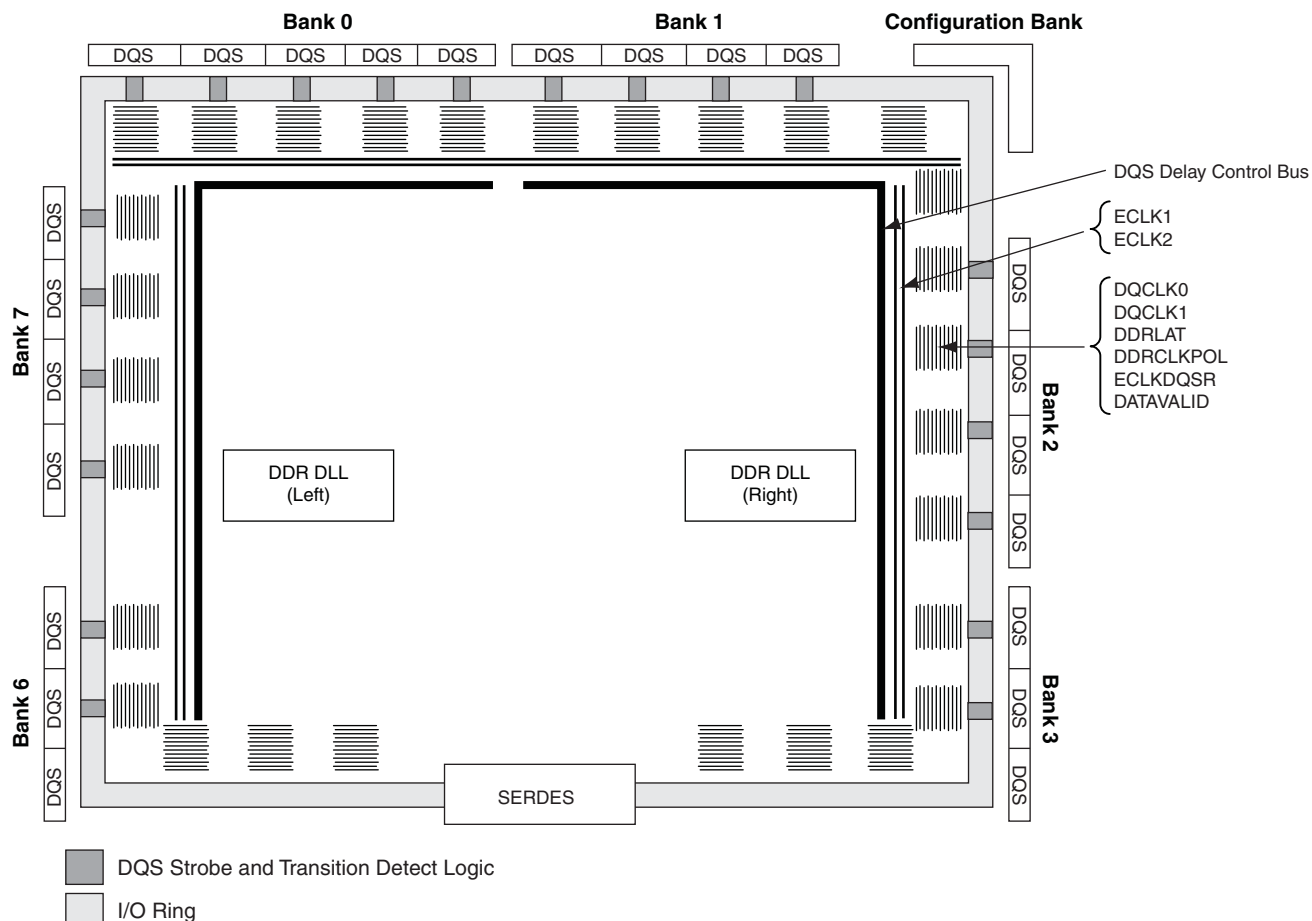
The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the ECLKDQSR (DDR Memory Interface mode) or ECLK (DDR Generic mode). The DDRLAT signal is used to ensure the data transfer from the synchronization registers to the clock transfer and gearbox registers.

The ECLKDQSR, DDRCLKPOL and DDRLAT signals are generated in the DQS Read Control Logic Block. See Figure 2-37 for an overview of the DQS read control logic.

Further discussion about using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.

Please see TN1180, [LatticeECP3 High-Speed I/O Interface](#) for more information on this topic.

Figure 2-36. Edge Clock, DLL Calibration and DQS Local Bus Distribution



*Includes shared configuration I/Os and dedicated configuration I/Os.

Please see TN1177, [LatticeECP3 sysIO Usage Guide](#) for on-chip termination usage and value ranges.

Equalization Filter

Equalization filtering is available for single-ended inputs on both true and complementary I/Os, and for differential inputs on the true I/Os on the left, right, and top sides. Equalization is required to compensate for the difficulty of sampling alternating logic transitions with a relatively slow slew rate. It is considered the most useful for the Input DDRX2 modes, used in DDR3 memory, LVDS, or TRLVDS signaling. Equalization filter acts as a tunable filter with settings to determine the level of correction. In the LatticeECP3 devices, there are four settings available: 0 (none), 1, 2 and 3. The default setting is 0. The equalization logic resides in the sysIO buffers, the two bits of setting is set uniquely in each input IOLOGIC block. Therefore, each sysIO can have a unique equalization setting within a DQS-12 group.

Hot Socketing

LatticeECP3 devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. Please refer to the Hot Socketing Specifications in the DC and Switching Characteristics in this data sheet.

SERDES and PCS (Physical Coding Sublayer)

LatticeECP3 devices feature up to 16 channels of embedded SERDES/PCS arranged in quads at the bottom of the devices supporting up to 3.2Gbps data rate. Figure 2-40 shows the position of the quad blocks for the LatticeECP3-150 devices. Table 2-14 shows the location of available SERDES Quads for all devices.

The LatticeECP3 SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express 1.1
- Ethernet (XAUI, GbE - 1000 Base CS/SX/LX and SGMII)
- Serial RapidIO
- SMPTE SDI (3G, HD, SD)
- CPRI
- SONET/SDH (STS-3, STS-12, STS-48)

Each quad contains four dedicated SERDES for high speed, full duplex serial data transfer. Each quad also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in quads, multiple baud rates can be supported within a quad with the use of dedicated, per channel $\div 1$, $\div 2$ and $\div 11$ rate dividers. Additionally, multiple quads can be arranged together to form larger data pipes.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, please refer to TN1176, [LatticeECP3 SERDES/PCS Usage Guide](#).

LatticeECP3 Supply Current (Standby)^{1, 2, 3, 4, 5, 6}

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical		Units
			-6L, -7L, -8L	-6, -7, -8	
I _{CC}	Core Power Supply Current	ECP-17EA	29.8	49.4	mA
		ECP3-35EA	53.7	89.4	mA
		ECP3-70EA	137.3	230.7	mA
		ECP3-95EA	137.3	230.7	mA
		ECP3-150EA	219.5	370.9	mA
I _{CCAUX}	Auxiliary Power Supply Current	ECP-17EA	18.3	19.4	mA
		ECP3-35EA	19.6	23.1	mA
		ECP3-70EA	26.5	32.4	mA
		ECP3-95EA	26.5	32.4	mA
		ECP3-150EA	37.0	45.7	mA
I _{CCPLL}	PLL Power Supply Current (Per PLL)	ECP-17EA	0.0	0.0	mA
		ECP3-35EA	0.1	0.1	mA
		ECP3-70EA	0.1	0.1	mA
		ECP3-95EA	0.1	0.1	mA
		ECP3-150EA	0.1	0.1	mA
I _{CCIO}	Bank Power Supply Current (Per Bank)	ECP-17EA	1.3	1.4	mA
		ECP3-35EA	1.3	1.4	mA
		ECP3-70EA	1.4	1.5	mA
		ECP3-95EA	1.4	1.5	mA
		ECP3-150EA	1.4	1.5	mA
I _{CCJ}	JTAG Power Supply Current	All Devices	2.5	2.5	mA
I _{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	ECP-17EA	6.1	6.1	mA
		ECP3-35EA	6.1	6.1	mA
		ECP3-70EA	18.3	18.3	mA
		ECP3-95EA	18.3	18.3	mA
		ECP3-150EA	24.4	24.4	mA

1. For further information on supply current, please see the list of technical documentation at the end of this data sheet.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.

3. Frequency 0 MHz.

4. Pattern represents a "blank" configuration data file.

5. T_J = 85 °C, power supplies at nominal voltage.

6. To determine the LatticeECP3 peak start-up current data, use the Power Calculator tool.

sysI/O Single-Ended DC Electrical Characteristics

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL}^1 (mA)	I_{OH}^1 (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)				
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	$V_{CCIO} - 0.4$	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS18	-0.3	$0.35 V_{CCIO}$	$0.65 V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	16, 12, 8, 4	-16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS15	-0.3	$0.35 V_{CCIO}$	$0.65 V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	8, 4	-8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS12	-0.3	$0.35 V_{CC}$	$0.65 V_{CC}$	3.6	0.4	$V_{CCIO} - 0.4$	6, 2	-6, -2
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVTTTL33	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
PCI33	-0.3	$0.3 V_{CCIO}$	$0.5 V_{CCIO}$	3.6	$0.1 V_{CCIO}$	$0.9 V_{CCIO}$	1.5	-0.5
SSTL18_I	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.4	$V_{CCIO} - 0.4$	6.7	-6.7
SSTL18_II (DDR2 Memory)	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.28	$V_{CCIO} - 0.28$	8	-8
							11	-11
SSTL2_I	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.54	$V_{CCIO} - 0.62$	7.6	-7.6
							12	-12
SSTL2_II (DDR Memory)	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.35	$V_{CCIO} - 0.43$	15.2	-15.2
							20	-20
SSTL3_I	-0.3	$V_{REF} - 0.2$	$V_{REF} + 0.2$	3.6	0.7	$V_{CCIO} - 1.1$	8	-8
SSTL3_II	-0.3	$V_{REF} - 0.2$	$V_{REF} + 0.2$	3.6	0.5	$V_{CCIO} - 0.9$	16	-16
SSTL15 (DDR3 Memory)	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.3	$V_{CCIO} - 0.3$	7.5	-7.5
						$V_{CCIO} * 0.8$	9	-9
HSTL15_I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
HSTL18_I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.4	$V_{CCIO} - 0.4$	8	-8
							12	-12
HSTL18_II	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.4	$V_{CCIO} - 0.4$	16	-16

1. For electromigration, the average DC current drawn by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed $n * 8$ mA, where n is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

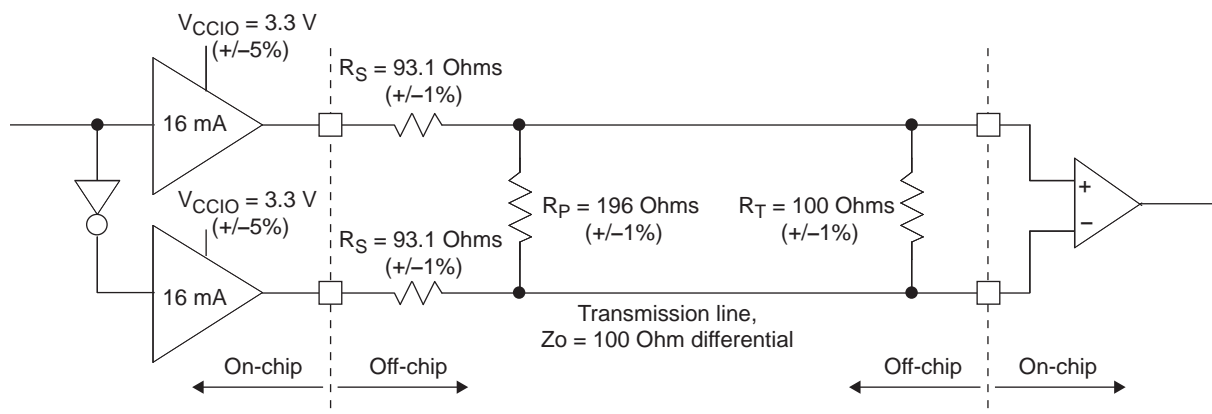


Table 3-3. LVPECL33 DC Conditions¹

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (+/-1%)	93	Ω
R_P	Driver Parallel Resistor (+/-1%)	196	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Inputs with Clock and Data (>10bits wide) are Aligned at Pin (GDDR2_RX.ECLK.Aligned) (No CLKDIV)									
Left and Right Sides Using DLLCLKPIN for Clock Input									
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-150EA	—	460	—	385	—	345	MHz
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-70EA/95EA	—	460	—	385	—	311	MHz
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-35EA	—	460	—	385	—	311	MHz
t _{DVACKGDDR}	Data Setup Before CLK (Left and Right Sides)	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-17EA	—	460	—	385	—	311	MHz
Top Side Using PCLK Pin for Clock Input									
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-150EA	—	235	—	170	—	130	MHz
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170	—	130	MHz
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-35EA	—	235	—	170	—	130	MHz
t _{DVACKGDDR}	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDR2_RX.DQS.Centered) Using DQS Pin for Clock Input									
Left and Right Sides									
t _{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
t _{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
f _{MAX_GDDR}	DDR2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Aligned at Pin (GDDR2_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Left and Right Sides									
t _{DVACKGDDR}	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX1 Output with Clock and Data (>10 Bits Wide) Centered at Pin (GDDR1_TX.SCLK.Centered) ¹⁰									
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps

LatticeECP3 Maximum I/O Buffer Speed ^{1, 2, 3, 4, 5, 6}

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
Maximum Input Frequency			
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	400	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	400	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	400	MHz
PPLVDS	Point-to-Point LVDS	400	MHz
TRLVDS	Transition-Reduced LVDS	612	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3\text{ V}$	400	MHz
HSTL18 (all supported classes)	HSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	400	MHz
HSTL15	HSTL_15 class I, $V_{CCIO} = 1.5\text{ V}$	400	MHz
SSTL33 (all supported classes)	SSTL_3 class I, II, $V_{CCIO} = 3.3\text{ V}$	400	MHz
SSTL25 (all supported classes)	SSTL_2 class I, II, $V_{CCIO} = 2.5\text{ V}$	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	400	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3\text{ V}$	166	MHz
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	166	MHz
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	166	MHz
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	166	MHz
LVC MOS15	LVC MOS 1.5, $V_{CCIO} = 1.5\text{ V}$	166	MHz
LVC MOS12	LVC MOS 1.2, $V_{CCIO} = 1.2\text{ V}$	166	MHz
PCI33	PCI, $V_{CCIO} = 3.3\text{ V}$	66	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	300	MHz
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	612	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	300	MHz
RS DS25	RS DS, Emulated, $V_{CCIO} = 2.5\text{ V}$	612	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	300	MHz
PPLVDS	Point-to-point LVDS	612	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3\text{ V}$	612	MHz
Mini-LVDS	Mini LVDS	612	MHz
HSTL18 (all supported classes)	HSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	200	MHz
HSTL15 (all supported classes)	HSTL_15 class I, $V_{CCIO} = 1.5\text{ V}$	200	MHz
SSTL33 (all supported classes)	SSTL_3 class I, II, $V_{CCIO} = 3.3\text{ V}$	233	MHz
SSTL25 (all supported classes)	SSTL_2 class I, II, $V_{CCIO} = 2.5\text{ V}$	233	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8\text{ V}$	266	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3\text{ V}$	166	MHz
LVC MOS33 (For all drives)	LVC MOS, 3.3 V	166	MHz
LVC MOS25 (For all drives)	LVC MOS, 2.5 V	166	MHz
LVC MOS18 (For all drives)	LVC MOS, 1.8 V	166	MHz
LVC MOS15 (For all drives)	LVC MOS, 1.5 V	166	MHz
LVC MOS12 (For all drives except 2 mA)	LVC MOS, $V_{CCIO} = 1.2\text{ V}$	166	MHz
LVC MOS12 (2 mA drive)	LVC MOS, $V_{CCIO} = 1.2\text{ V}$	100	MHz

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Clock	Min.	Typ.	Max.	Units
f _{IN}	Input clock frequency (CLKI, CLKFB)		Edge clock	2	—	500	MHz
			Primary clock ⁴	2	—	420	MHz
f _{OUT}	Output clock frequency (CLKOP, CLKOS)		Edge clock	4	—	500	MHz
			Primary clock ⁴	4	—	420	MHz
f _{OUT1}	K-Divider output frequency	CLKOK		0.03125	—	250	MHz
f _{OUT2}	K2-Divider output frequency	CLKOK2		0.667	—	166	MHz
f _{VCO}	PLL VCO frequency			500	—	1000	MHz
f _{PFD} ³	Phase detector input frequency		Edge clock	2	—	500	MHz
			Primary clock ⁴	2	—	420	MHz
AC Characteristics							
t _{PA}	Programmable delay unit			65	130	260	ps
t _{DT}	Output clock duty cycle (CLKOS, at 50% setting)		Edge clock	45	50	55	%
		f _{OUT} ≤ 250 MHz	Primary clock	45	50	55	%
		f _{OUT} > 250 MHz	Primary clock	30	50	70	%
t _{CPA}	Coarse phase shift error (CLKOS, at all settings)			-5	0	+5	% of period
t _{OPW}	Output clock pulse width high or low (CLKOS)			1.8	—	—	ns
t _{OPJIT} ¹	Output clock period jitter	f _{OUT} ≥ 420 MHz		—	—	200	ps
		420 MHz > f _{OUT} ≥ 100 MHz		—	—	250	ps
		f _{OUT} < 100 MHz		—	—	0.025	UIPP
t _{SK}	Input clock to output clock skew when N/M = integer			—	—	500	ps
t _{LOCK} ²	Lock time	2 to 25 MHz		—	—	200	us
		25 to 500 MHz		—	—	50	us
t _{UNLOCK}	Reset to PLL unlock time to ensure fast reset			—	—	50	ns
t _{HI}	Input clock high time	90% to 90%		0.5	—	—	ns
t _{LO}	Input clock low time	10% to 10%		0.5	—	—	ns
t _{IPJIT}	Input clock period jitter			—	—	400	ps
t _{RST}	Reset signal pulse width high, RSTK			10	—	—	ns
	Reset signal pulse width high, RST			500	—	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 4$ MHz. For $f_{PFD} < 4$ MHz, the jitter numbers may not be met in certain conditions. Please contact the factory for $f_{PFD} < 4$ MHz.
4. When using internal feedback, maximum can be up to 500 MHz.

SERDES/PCS Block Latency

Table 3-8 describes the latency of each functional block in the transmitter and receiver. Latency is given in parallel clock cycles. Figure 3-12 shows the location of each block.

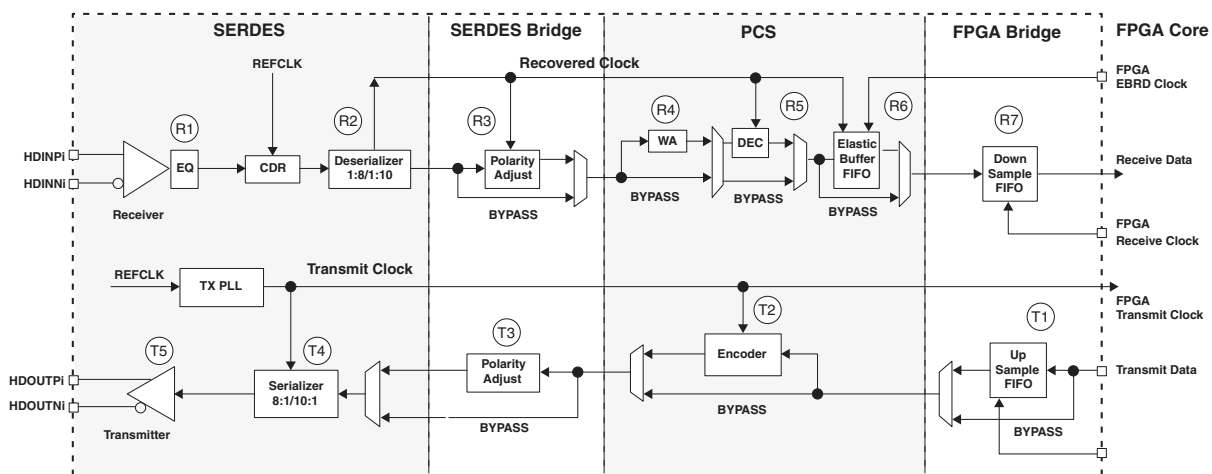
Table 3-8. SERDES/PCS Latency Breakdown

Item	Description	Min.	Avg.	Max.	Fixed	Bypass	Units
Transmit Data Latency¹							
T1	FPGA Bridge - Gearing disabled with different clocks	1	3	5	—	1	word clk
	FPGA Bridge - Gearing disabled with same clocks	—	—	—	3	1	word clk
	FPGA Bridge - Gearing enabled	1	3	5	—	—	word clk
T2	8b10b Encoder	—	—	—	2	1	word clk
T3	SERDES Bridge transmit	—	—	—	2	1	word clk
T4	Serializer: 8-bit mode	—	—	—	15 + $\Delta 1$	—	UI + ps
	Serializer: 10-bit mode	—	—	—	18 + $\Delta 1$	—	UI + ps
T5	Pre-emphasis ON	—	—	—	1 + $\Delta 2$	—	UI + ps
	Pre-emphasis OFF	—	—	—	0 + $\Delta 3$	—	UI + ps
Receive Data Latency²							
R1	Equalization ON	—	—	—	$\Delta 1$	—	UI + ps
	Equalization OFF	—	—	—	$\Delta 2$	—	UI + ps
R2	Deserializer: 8-bit mode	—	—	—	10 + $\Delta 3$	—	UI + ps
	Deserializer: 10-bit mode	—	—	—	12 + $\Delta 3$	—	UI + ps
R3	SERDES Bridge receive	—	—	—	2	—	word clk
R4	Word alignment	3.1	—	4	—	—	word clk
R5	8b10b decoder	—	—	—	1	—	word clk
R6	Clock Tolerance Compensation	7	15	23	1	1	word clk
R7	FPGA Bridge - Gearing disabled with different clocks	1	3	5	—	1	word clk
	FPGA Bridge - Gearing disabled with same clocks	—	—	—	3	1	word clk
	FPGA Bridge - Gearing enabled	1	3	5	—	—	word clk

1. $\Delta 1 = -245$ ps, $\Delta 2 = +88$ ps, $\Delta 3 = +112$ ps.

2. $\Delta 1 = +118$ ps, $\Delta 2 = +132$ ps, $\Delta 3 = +700$ ps.

Figure 3-12. Transmitter and Receiver Latency Block Diagram



Serial Rapid I/O Type 2/CPRI LV E.24 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}^1	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX_DIFF_DC}$	Differential impedance		80	100	120	Ohms
$J_{TX_DDJ}^{3, 4, 5}$	Output data deterministic jitter		—	—	0.17	UI
$J_{TX_TJ}^{2, 3, 4, 5}$	Total output data jitter		—	—	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
$J_{RX_DJ}^{2, 3, 4, 5}$	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
$J_{RX_RJ}^{2, 3, 4, 5}$	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
$J_{RX_SJ}^{2, 3, 4, 5}$	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
$J_{RX_TJ}^{1, 2, 3, 4, 5}$	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-19. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR _{SDO}	Serial data rate		270	—	2975	Mbps
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ^{1,2}	Serial output jitter, alignment	2970Mbps	—	—	0.30	UI
T _{JTIMING}	Serial output jitter, timing	270 Mbps	—	—	0.20	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mbps	—	—	1.0	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mbps	—	—	2.0	UI

Notes:

- Timing jitter is measured in accordance with SMPTE RP 184-1996, SMPTE RP 192-1996 and the applicable serial data transmission standard, SMPTE 259M-1997 or SMPTE 292M (proposed). A color bar test pattern is used. The value of f_{SCLK} is 270 MHz or 360 MHz for SMPTE 259M, 540 MHz for SMPTE 344M or 1485 MHz for SMPTE 292M serial data rates. See the Timing Jitter Bandpass section.
- Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
- All Tx jitter is measured at the output of an industry standard cable driver; connection to the cable driver is via a 50 Ohm impedance differential signal from the Lattice SERDES device.
- The cable driver drives: RL=75 Ohm, AC-coupled at 270, 1485, or 2970 Mbps, RREFLVL=RREFPRE=4.75 kOhm 1%.

Table 3-20. Receive

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR _{SDI}	Serial input data rate		270	—	2970	Mbps
CID	Stream of non-transitions (=Consecutive Identical Digits)		7(3G)/26(SMPTE Triple rates) @ 10-12 BER	—	—	Bits

Table 3-21. Reference Clock

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
F _{VCLK}	Video output clock frequency		27	—	74.25	MHz
DC _V	Duty cycle, video clock		45	50	55	%

LatticeECP3 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description		Min.	Max.	Units
POR, Configuration Initialization, and Wakeup					
t _{ICFG}	Time from the Application of V _{CC} , V _{CCAUX} or V _{CCIO8} * (Whichever is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Master mode	—	23	ms
		Slave mode	—	6	ms
t _{VMC}	Time from t _{ICFG} to the Valid Master MCLK		—	5	μs
t _{PRGM}	PROGRAMN Low Time to Start Configuration		25	—	ns
t _{PRGMRJ}	PROGRAMN Pin Pulse Rejection		—	10	ns
t _{DPPINIT}	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
t _{DPPDONE}	Delay Time from PROGRAMN Low to DONE Low		—	37	ns
t _{DINIT} ¹	PROGRAMN High to INITN High Delay		—	1	ms
t _{MWC}	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t _{CZ}	MCLK From Active To Low To High-Z		—	300	ns
t _{IODISS}	User I/O Disable from PROGRAMN Low		—	100	ns
t _{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence		—	100	ns
All Configuration Modes					
t _{SUCDI}	Data Setup Time to CCLK/MCLK		5	—	ns
t _{HCDI}	Data Hold Time to CCLK/MCLK		1	—	ns
t _{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode		-0.2	12	ns
Slave Serial					
t _{SSCH}	CCLK Minimum High Pulse		5	—	ns
t _{SSCL}	CCLK Minimum Low Pulse		5	—	ns
f _{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave Parallel					
t _{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t _{HCS}	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t _{SUWD}	WRITEN Setup Time to CCLK/MCLK		7	—	ns
t _{HWD}	WRITEN Hold Time to CCLK/MCLK		1	—	ns
t _{DCB}	CCLK/MCLK to BUSY Delay Time		—	12	ns
t _{CORD}	CCLK to Out for Read Data		—	12	ns
t _{BSCH}	CCLK Minimum High Pulse		6	—	ns
t _{BSCL}	CCLK Minimum Low Pulse		6	—	ns
t _{BSCYC}	Byte Slave Cycle Time		30	—	ns
f _{CCLK}	CCLK/MCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave SPI					
t _{CFGX}	INITN High to MCLK Low		—	80	ns
t _{CSSPI}	INITN High to CSSPIN Low		0.2	2	μs
t _{SOCDO}	MCLK Low to Output Valid		—	15	ns
t _{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time		0.3		μs
f _{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
t _{SSCH}	CCLK Minimum High Pulse		5	—	ns

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95EA			ECP3-150EA	
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43	30	47
	Bank 1	18	24	39	24	43
	Bank 2	8	12	13	12	18
	Bank 3	20	23	33	23	37
	Bank 6	22	25	33	25	37
	Bank 7	11	16	18	16	24
	Bank 8	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	6	9	9	9	15
	Bank 3	9	12	16	12	21
	Bank 6	11	14	16	14	21
	Bank 7	9	12	13	12	18
	Bank 8	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43	60/30	94/47
	Bank 1	36/18	48/24	78/39	48/24	86/43
	Bank 2	28/14	42/21	44/22	42/21	66/33
	Bank 3	58/29	71/35	98/49	71/35	116/58
	Bank 6	67/33	78/39	98/49	78/39	116/58
	Bank 7	40/20	56/28	62/31	56/28	84/42
	Bank 8	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank	Bank 0	3	5	7	5	7
	Bank 1	3	4	7	4	7
	Bank 2	2	3	3	3	4
	Bank 3	3	4	5	4	7
	Bank 6	4	4	5	4	7
	Bank 7	3	4	4	4	6
	Configuration Bank8	0	0	0	0	0
SERDES Quads		1	2	3	2	4

1. These pins must remain floating on the board.

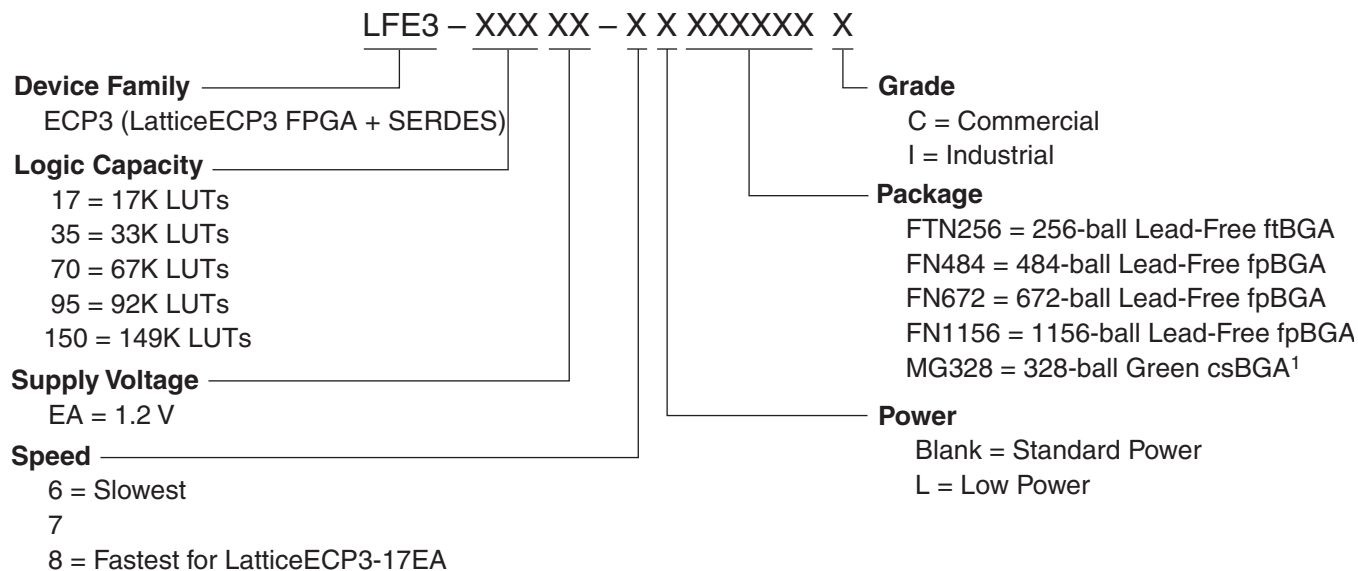


LatticeECP3 Family Data Sheet Ordering Information

April 2014

Data Sheet DS1021

LatticeECP3 Part Number Description



1. Green = Halogen free and lead free.

Ordering Information

LatticeECP3 devices have top-side markings, for commercial and industrial grades, as shown below:

Commercial	Industrial
<div>LATTICE LFE3-95EA 7FN672C Datecode</div>	<div>LATTICE LFE3-95EA 7FN672I Datecode</div>

Note: See [PCN 05A-12](#) for information regarding a change to the top-side mark logo.

For Further Information

A variety of technical notes for the LatticeECP3 family are available on the Lattice website at www.latticesemi.com.

- TN1169, [LatticeECP3 sysCONFIG Usage Guide](#)
- TN1176, [LatticeECP3 SERDES/PCS Usage Guide](#)
- TN1177, [LatticeECP3 sysIO Usage Guide](#)
- TN1178, [LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide](#)
- TN1179, [LatticeECP3 Memory Usage Guide](#)
- TN1180, [LatticeECP3 High-Speed I/O Interface](#)
- TN1181, [Power Consumption and Management for LatticeECP3 Devices](#)
- TN1182, [LatticeECP3 sysDSP Usage Guide](#)
- TN1184, [LatticeECP3 Soft Error Detection \(SED\) Usage Guide](#)
- TN1189, [LatticeECP3 Hardware Checklist](#)
- TN1215, [LatticeECP2MS and LatticeECP2S Devices](#)
- TN1216, [LatticeECP2/M and LatticeECP3 Dual Boot Feature Advanced Security Encryption Key Programming Guide for LatticeECP3](#)
- TN1222, [LatticeECP3 Slave SPI Port User's Guide](#)

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTTL, LVCMOS, SSTL, HSTL): www.jedec.org
- PCI: www.pcisig.com